

# NPN RF POWER TRANSISTOR

**DESCRIPTION:**

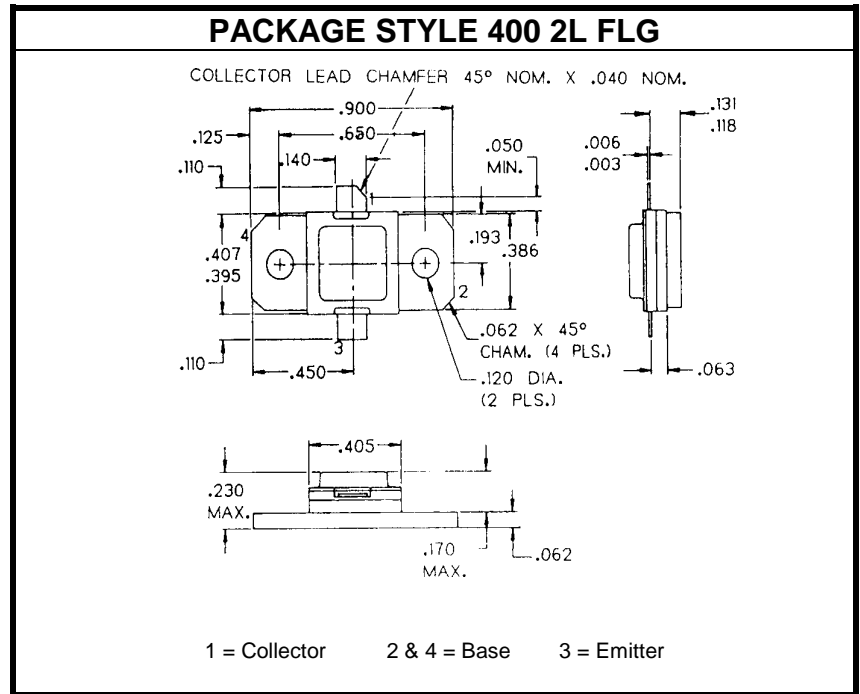
The **ASAT35L** is a Common Base Transistor Designed for L-Band Satcom Amplifier Applications.

**FEATURES INCLUDE:**

- Input/Output Matching Networks
- Gold Metallization
- Emitter Ballasting

**MAXIMUM RATINGS**

$I_C$	3.5 A
$V_{CBO}$	50 V
$P_{DISS}$	55 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-55^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-55^\circ\text{C}$ to $+200^\circ\text{C}$
$\theta_{JC}$	2.6 $^\circ\text{C/W}$


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 20\text{ mA}$			50			V
$BV_{CES}$	$I_C = 20\text{ mA}$			50			V
$BV_{EBO}$	$I_E = 10\text{ mA}$			3.5			V
$I_{CES}$	$V_{CE} = 28\text{ V}$					5.0	mA
$h_{FE}$	$V_{CE} = 5\text{ V}$	$I_C = 2.0\text{ A}$		20		300	---
$P_G$ $\eta_c$	$V_{CE} = 28\text{ V}$	$P_{OUT} = 35\text{ W}$	$f = 1500 - 1600\text{ MHz}$	8.0 45	9.0 50		dB %
$Z_{CL}$ $Z_{IN}$	$V_{CE} = 28\text{ V}$	$P_{OUT} = 35\text{ W}$	$f = 1500\text{ MHz}$	3.0 + j0.5 4.0 + j15.0			Ohms
$Z_{CL}$ $Z_{IN}$	$V_{CE} = 28\text{ V}$	$P_{OUT} = 35\text{ W}$	$f = 1600\text{ MHz}$	1.8 + j1.0 5.5 + j16.2			Ohms